

In a photoelectric conversion device comprising a first-conductivity type first semiconductor region located in a pixel region, a second-conductivity type second semiconductor region provided in the first semiconductor region, and a wiring for electrically connecting the second semiconductor region to a circuit element located outside the pixel region, a shield is provided on the light-incident side of the wiring, via an insulator in such a way that it covers at least part of the wiring and also the shield comprises a conductor whose potential stands fixed.

This photoelectric conversion device may hardly be affected with low-frequency radiated noises as typified by power-source noise.